

IRFH7921TRPBF-VB Datasheet

N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^{a, e}	Q_g (Typ)
30	0.007 at $V_{GS} = 10$ V	80	31 nC
	0.009 at $V_{GS} = 4.5$ V	60	

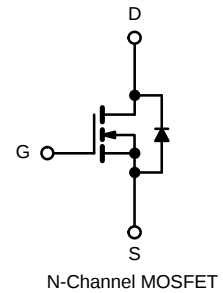
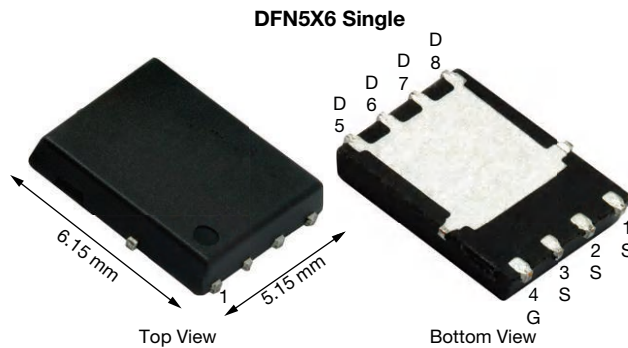
FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2011/65/EU


RoHS
 COMPLIANT

APPLICATIONS

- OR-ing
- Server
- DC/DC



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 175^\circ\text{C}$)	I_D	80	A
		60	
		50 ^{b, c}	
		45 ^{b, c}	
Pulsed Drain Current	I_{DM}	210	mJ
Avalanche Current Pulse	I_{AS}	60	
Single Pulse Avalanche Energy	E_{AS}	95	
Continuous Source-Drain Diode Current	I_S	80	A
		60	
Maximum Power Dissipation	P_D	155	W
		105	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^{b, d}	$t \leq 10$ sec	R_{thJA}	32	40	$^\circ\text{C/W}$
Maximum Junction-to-Case	Steady State	R_{thJC}	0.5	0.6	

Notes:

a. Based on $T_C = 25^\circ\text{C}$.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10$ sec.

d. Maximum under steady state conditions is 90°C/W .

e. Calculated based on maximum junction temperature. Package limitation current is 90 A.

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	30			V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = 250 μA		35		mV/°C
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 7.5		
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.5		2.0	V
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			1	μA
		V _{DS} = 30 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	90			A
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 30.8 A		0.007		Ω
		V _{GS} = 4.5 V, I _D = 27 A		0.009		
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30.8 A		160		S
Dynamic ^b						
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz			1180	pF
Output Capacitance	C _{oss}				425	
Reverse Transfer Capacitance	C _{rss}				170	
Total Gate Charge	Q _g	V _{DS} = 15 V, V _{GS} = 10 V, I _D = 30.8 A			61	nC
		V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 27.8 A			31.5	
Gate-Source Charge	Q _{gs}				10	
Gate-Drain Charge	Q _{gd}				6	
Gate Resistance	R _g	f = 1 MHz		1.4	2.1	Ω
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 0.625 Ω I _D ≅ 24 A, V _{GEN} = 10 V, R _g = 1 Ω		18	27	ns
Rise Time	t _r			11	17	
Turn-Off Delay Time	t _{d(off)}			70	105	
Fall Time	t _f			10	15	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 15 V, R _L = 0.67 Ω I _D ≅ 22.5 A, V _{GEN} = 4.5 V, R _g = 1 Ω		55	83	
Rise Time	t _r			180	270	
Turn-Off Delay Time	t _{d(off)}			55	83	
Fall Time	t _f			12	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C		60		A
Pulse Diode Forward Current ^a	I _{SM}			210		
Body Diode Voltage	V _{SD}	I _S = 22 A		0.8	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20 A, di/dt = 100 A/μs, T _J = 25 °C		52	78	ns
Body Diode Reverse Recovery Charge	Q _{rr}			70.2	105	nC
Reverse Recovery Fall Time	t _a			27		ns
Reverse Recovery Rise Time	t _b			25		

Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



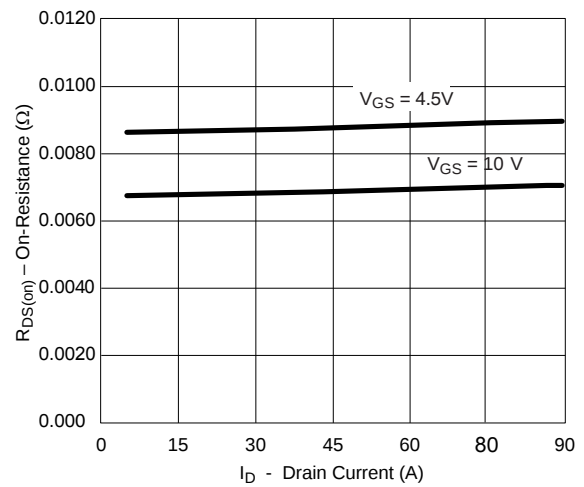
Output Characteristics



Transfer Characteristics



Transconductance



$R_{DS(on)}$ vs. Drain Current



Capacitance



Gate Charge

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



Forward Diode Voltage vs. Temperature



$R_{DS(on)}$ vs. V_{GS} vs. Temperature

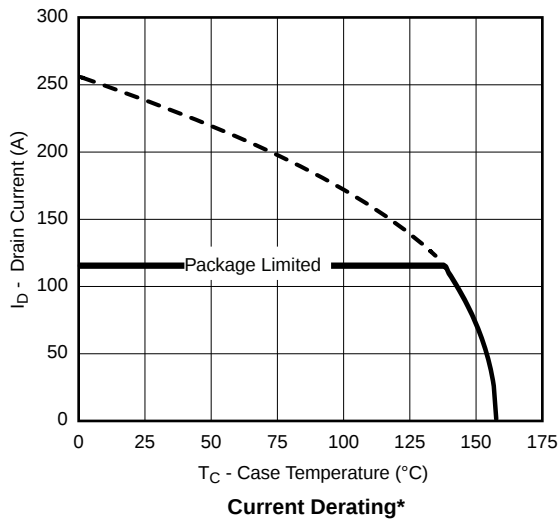


Threshold Voltage



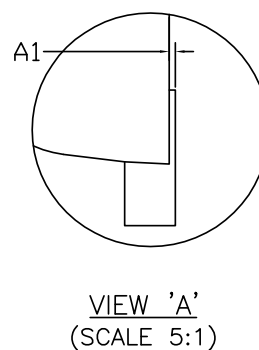
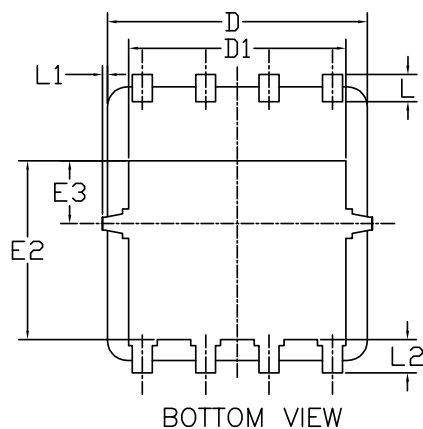
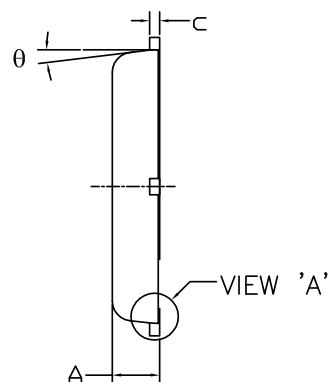
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



*The power dissipation P_D is based on $T_{J(max)} = 175$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Technical drawing of a stepped shaft (Fig. 1.10) showing dimensions in millimeters. The shaft has a total length of 6.15 mm and a maximum diameter of 4.60 mm. It features a central section with a diameter of 4.12 mm and a length of 4.60 mm. The left end has a diameter of 0.50 mm and a length of 1.60 mm. The right end has a diameter of 0.55 mm and a length of 0.65 mm. The central section has a diameter of 4.12 mm and a length of 4.60 mm. The shaft is shown in a cross-sectional view with a centerline.

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.

2. CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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